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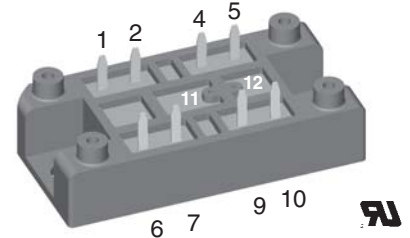
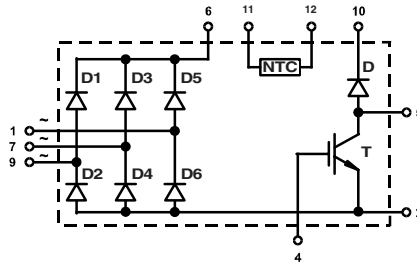
For any questions, you can email us directly:

sales@integrated-circuit.com

IXYS VUB 72

Three Phase Rectifier Bridge with Brake Chopper

V_{RRM} = 1200/1600 V
I_{dAVM} = 110 A



Input Rectifier D1 - D6

Symbol	Conditions	Maximum Ratings	
V _{RRM}	VUB 72 -12 NO1	1200	V
	VUB 72 -16 NO1	1600	V
I _{FAV}	T _C = 80°C; sine 180°	40	A
I _{dAVM}	T _C = 80°C; rectangular; d = 1/3; bridge	110	A
I _{FSM}	T _{VJ} = 25°C; t = 10 ms; sine 50 Hz	530	A
P _{tot}	T _C = 25°C	100	W

Features

- three phase mains rectifier
- brake chopper:
 - IGBT with low saturation voltage
 - HiPerFRED™ free wheeling diode
- module package:
 - high level of integration
 - solder terminals for PCB mounting
 - UL registered E72873
 - isolated DCB ceramic base plate
 - large creepage and strike distances
 - high reliability

Symbol	Conditions	Characteristic Values (T _{VJ} = 25°C, unless otherwise specified)		
		min.	typ.	max.
V _F	I _F = 25 A; T _{VJ} = 25°C		1.0	1.1 V
		T _{VJ} = 125°C	0.9	V
I _R	V _R = V _{RRM} ; T _{VJ} = 25°C V _R = 0.8 · V _{RRM} ; T _{VJ} = 125°C		0.4	0.02 mA
				mA
R _{thJC}	per diode			1.2 K/W
R _{thJH}	with heat transfer paste			1.42 K/W

Applications

- drives with
- mains input
 - DC link
 - inverter or chopper feeding the machine
 - motor and generator/brake operation

Chopper Diode D

Symbol	Conditions	Maximum Ratings	
V _{RRM}	T _{VJ} = 25°C to 150°C	1200	V
I _{F25}	DC; T _C = 25°C	25	A
I _{F80}	DC; T _C = 80°C	15	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V _F	I _F = 25 A; T _{VJ} = 25°C		2.7	3.1 V
		T _{VJ} = 125°C	2.0	V
I _R	V _R = V _{RRM} ; T _{VJ} = 25°C		0.1	0.1 mA
		T _{VJ} = 125°C		mA
I _{RM}	I _F = 15A; di _F /dt = -400 A/μs		16	A
		V _R = 600 V; T _{VJ} = 125°C	130	ns
R _{thJC}	with heat transfer paste			2.3 K/W
R _{thJH}				3.12 K/W

IXYS reserves the right to change limits, test conditions and dimensions.

IXYS VUB 72

Chopper Transistor T

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	1200	V
V_{GES}		± 20	V
I_{C25}	DC; $T_C = 25^{\circ}\text{C}$	50	A
I_{C80}	DC; $T_C = 80^{\circ}\text{C}$	35	A
I_{CM}	$V_{GE} = \pm 15\text{ V}; R_G = 39\ \Omega; T_{VJ} = 125^{\circ}\text{C}$	50	A
V_{CEK}	RBSOA; $L = 100\ \mu\text{H}$	V_{CES}	
t_{SC} (SCSOA)	$V_{GE} = \pm 15\text{ V}; V_{CE} = 900\text{ V}; T_{VJ} = 125^{\circ}\text{C}$ $R_G = 39\ \Omega$; non repetitive	10	μs

Symbol	Conditions ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)	Characteristic Values			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 25\text{ A}; V_{GE} = 15\text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.9 2.1	V V	
$V_{GE(th)}$	$I_C = 1\text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V	
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.1	0.1 mA mA	
I_{GES}	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$			200 nA	
$t_{d(on)}$ t_r $t_{d(off)}$ t_t E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600\text{ V}; I_C = 25\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 39\ \Omega$		80 50 440 50	ns ns ns ns	
				3.8 2.0	mJ mJ
C_{ies}		$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		2.0	nF
Q_{Gon}		$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 35\text{ A}$		150	nC
R_{thJC}					0.6 K/W
R_{thJH}		with heat transfer paste, see mounting instructions			1.2 K/W

Temperature Sensor NTC

Symbol	Conditions	Characteristic Values typ.	
R_{25}	$T = 25^{\circ}\text{C}$		2.2 k Ω
$B_{25/100}$			3560 K

$$R(T) = R_{25} \cdot e^{B_{25/100} \left(\frac{1}{T} - \frac{1}{298\text{K}} \right)}$$

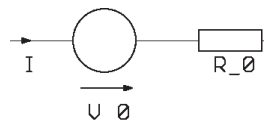
Module

Symbol	Conditions	Maximum Ratings	
I_{RMS}	per pin	100	A
T_{VJ}		-40...+150	$^{\circ}\text{C}$
T_{stg}		-40...+125	$^{\circ}\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}; t = 1\text{ min}$	3600	V~
M_d	Mounting torque (M5)	2 - 2.5	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_A, d_S		5		mm
Weight			35	g

Equivalent Circuits for Simulation

Conduction



D1 - D6

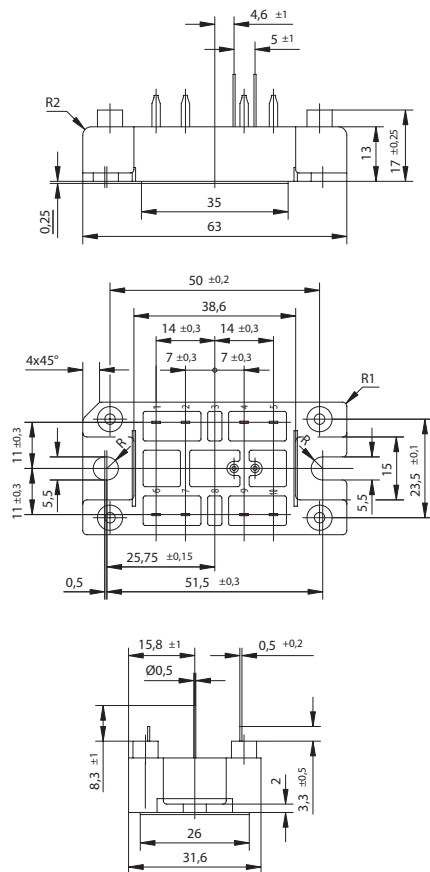
Diode (typ. at $T_J = 125^{\circ}\text{C}$)
 $V_0 = 0.85\text{ V}; R_0 = 7\text{ m}\Omega$

T/D

IGBT (typ. at $V_{GE} = 15\text{ V}; T_J = 125^{\circ}\text{C}$)
 $V_0 = 1.0\text{ V}; R_0 = 45\text{ m}\Omega$

Free Wheeling Diode (typ. at $T_J = 125^{\circ}\text{C}$)
 $V_0 = 1.25\text{ V}; R_0 = 32\text{ m}\Omega$

Dimensions in mm (1 mm = 0.0394")



Input Rectifier D1-D6

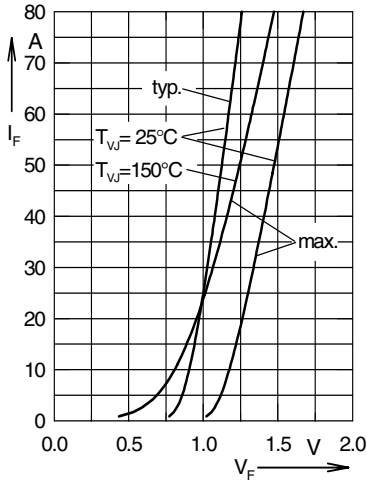


Fig. 1 Forward current vs. voltage drop per rectifier diode

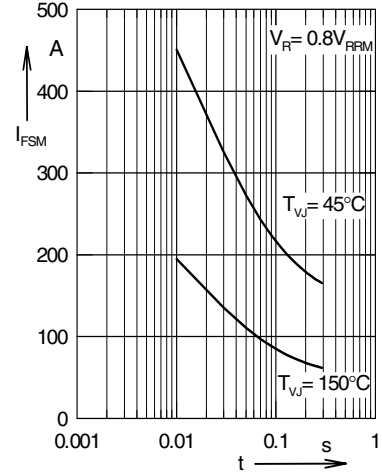


Fig. 2 Surge overload current per rectifier diode

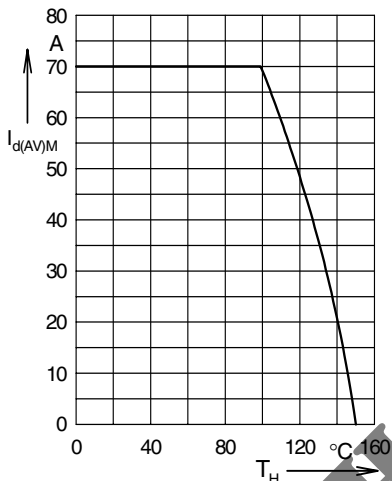


Fig. 3 Maximum forward current vs. heatsink temperature (Rectifier bridge)

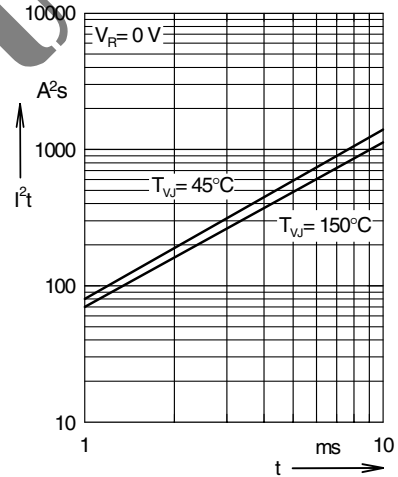


Fig. 4 I^2t versus time per rectifier diode

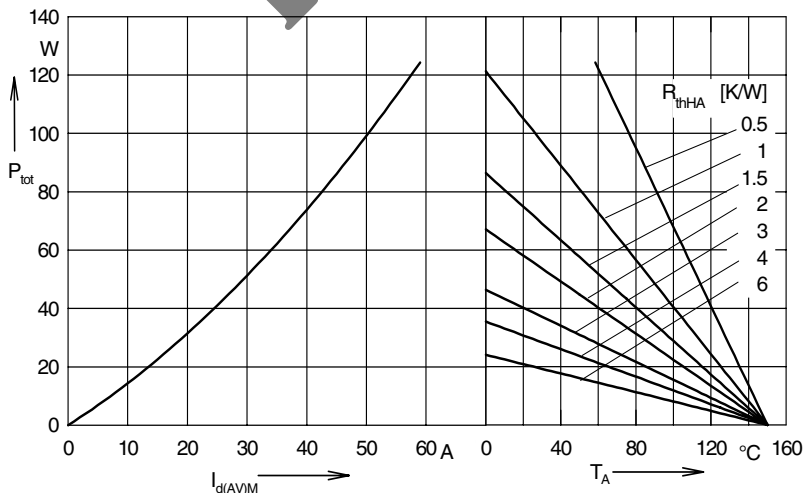


Fig. 5 Power dissipation vs. direct output current and ambient temperature (Rectifier bridge)

Note:
Transient thermal impedance
see next page

Chopper T - D

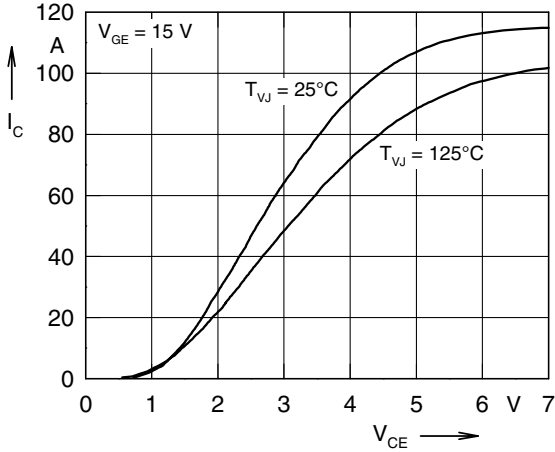


Fig. 6 Typ. IGBT output characteristics

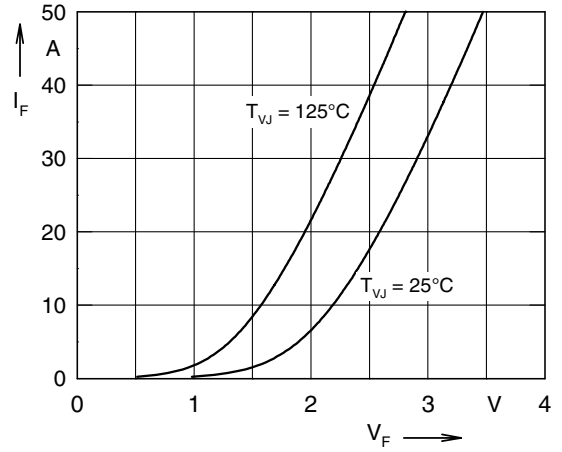


Fig. 7 Typ. forward characteristics of free wheeling diode

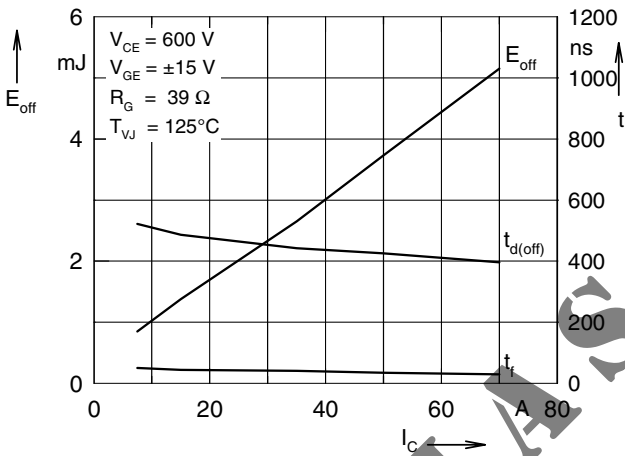


Fig. 8 Typ. IGBT turn off energy and switching times versus collector current

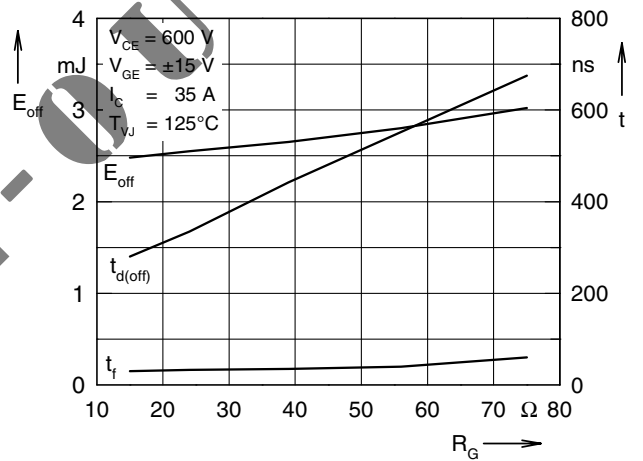


Fig. 9 Typ. IGBT turn off energy and switching times versus gate resistor

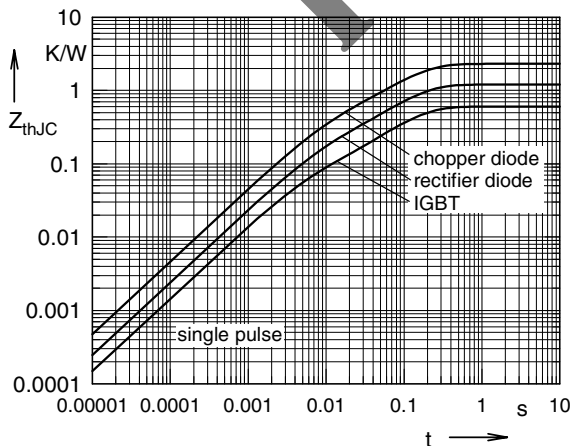


Fig. 10 Typ. transient thermal impedance

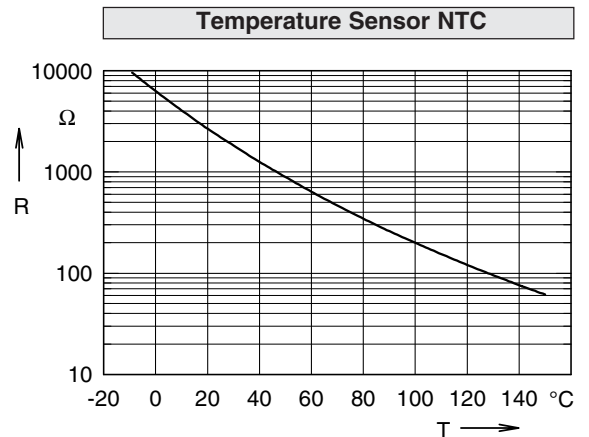


Fig. 11 Typ. thermistorresistance versus temperature